

74HC573; 74HCT573

Octal D-type transparent latch; 3-state

Rev. 6 — 26 January 2015

Product data sheet

1. General description

The 74HC573; 74HCT573 is a high-speed Si-gate CMOS device and is pin compatible with Low-power Schottky TTL (LSTTL). It is specified in compliance with JEDEC standard no. 7A.

The 74HC573; 74HCT573 has octal D-type transparent latches featuring separate D-type inputs for each latch and 3-state true outputs for bus-oriented applications. A latch enable (LE) input and an output enable ($\overline{OE}$) input are common to all latches.

When LE is HIGH, data at the Dn inputs enter the latches. In this condition, the latches are transparent, i.e. a latch output changes state each time its corresponding D input changes.

When LE is LOW the latches store the information that was present at the D-inputs a set-up time preceding the HIGH-to-LOW transition of LE. When $\overline{OE}$ is LOW, the contents of the 8 latches are available at the outputs. When $\overline{OE}$ is HIGH, the outputs go to the high-impedance OFF-state. Operation of the $\overline{OE}$ input does not affect the state of the latches.

The 74HC573; 74HCT573 is functionally identical to:

- 74HC563; 74HCT563, but inverted outputs
- 74HC373; 74HCT373, but different pin arrangement

2. Features and benefits

- Input levels:
 - ◆ For 74HC573: CMOS level
 - ◆ For 74HCT573: TTL level
- Inputs and outputs on opposite sides of package allowing easy interface with microprocessors
- Useful as input or output port for microprocessors and microcomputers
- 3-state non-inverting outputs for bus-oriented applications
- Common 3-state output enable input
- Multiple package options
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2 000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC573N	-40 °C to +125 °C	DIP20	plastic dual in-line package; 20 leads (300 mil)	SOT146-1
74HCT534N				
74HC573D	-40 °C to +125 °C	SO20	plastic small outline package; 20 leads; body width 7.5 mm	SOT163-1
74HCT573D				
74HC573DB	-40 °C to +125 °C	SSOP20	plastic shrink small outline package; 20 leads; body width 5.3 mm	SOT339-1
74HCT573DB				
74HC573PW	-40 °C to +125 °C	TSSOP20	plastic thin shrink small outline package; 20 leads; body width 4.4 mm	SOT360-1
74HCT573PW				
74HC573BQ	-40 °C to +125 °C	DHVQFN20	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 20 terminals; body 2.5 × 4.5 × 0.85 mm	SOT764-1
74HCT573BQ				

4. Functional diagram

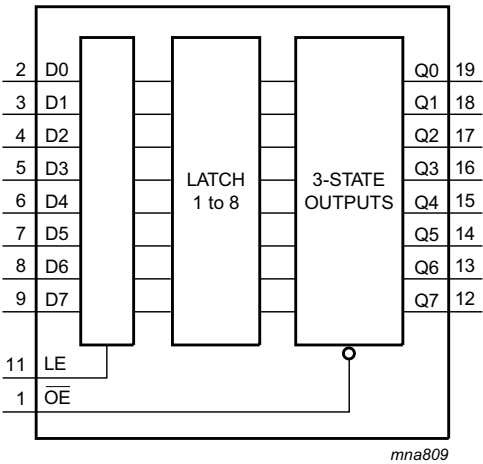
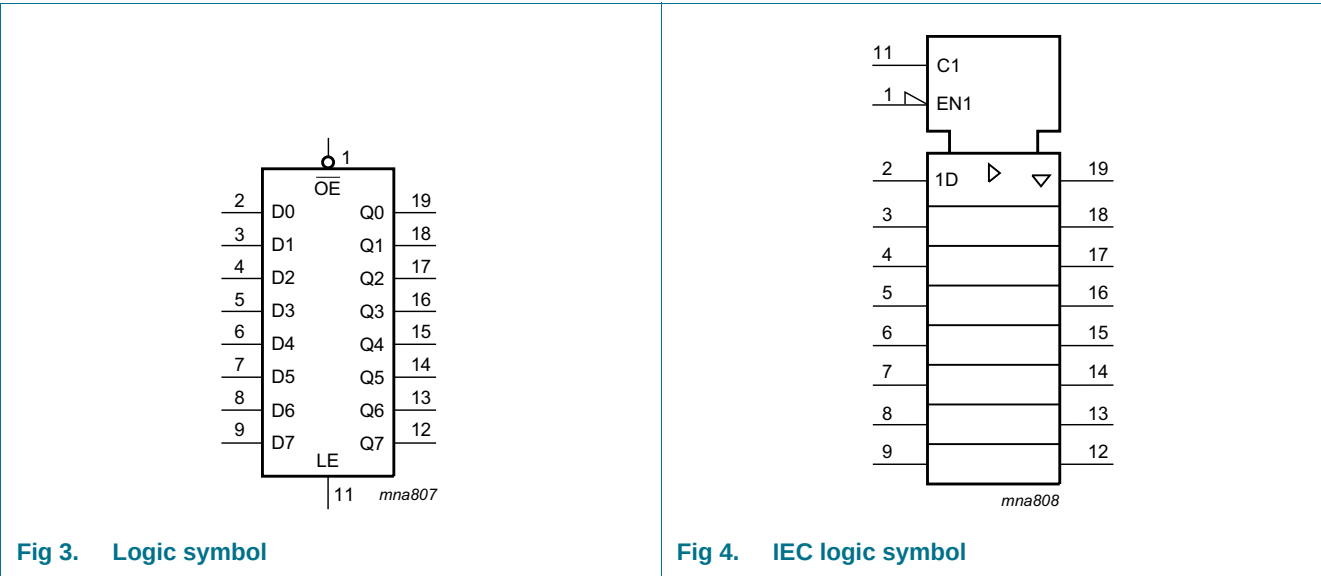
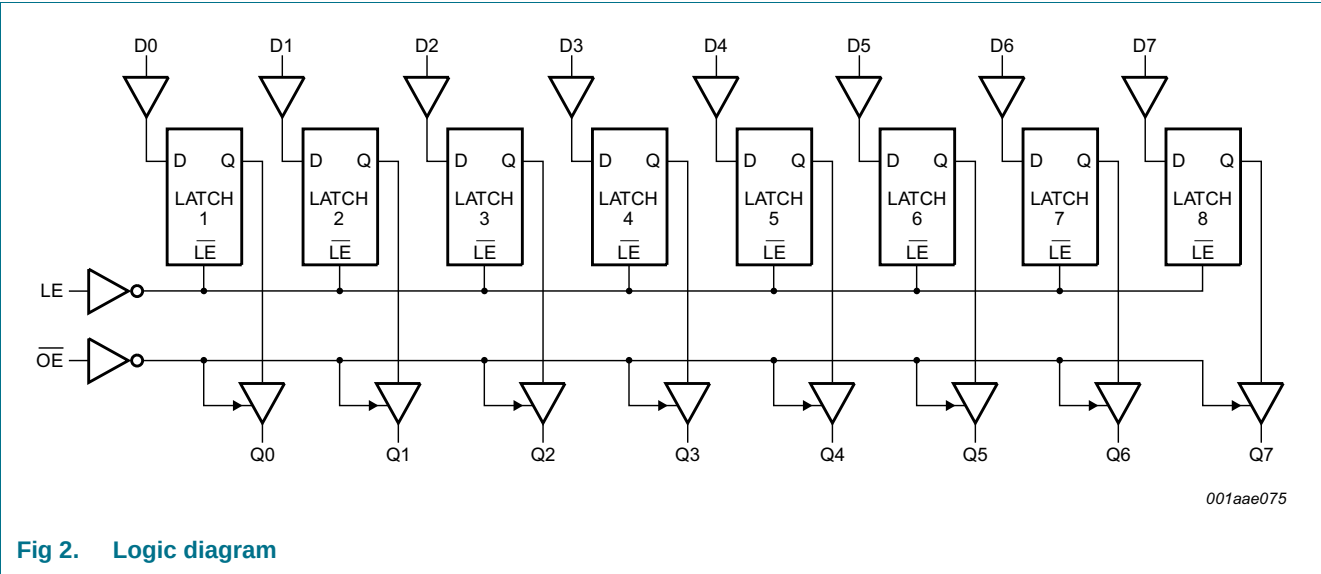
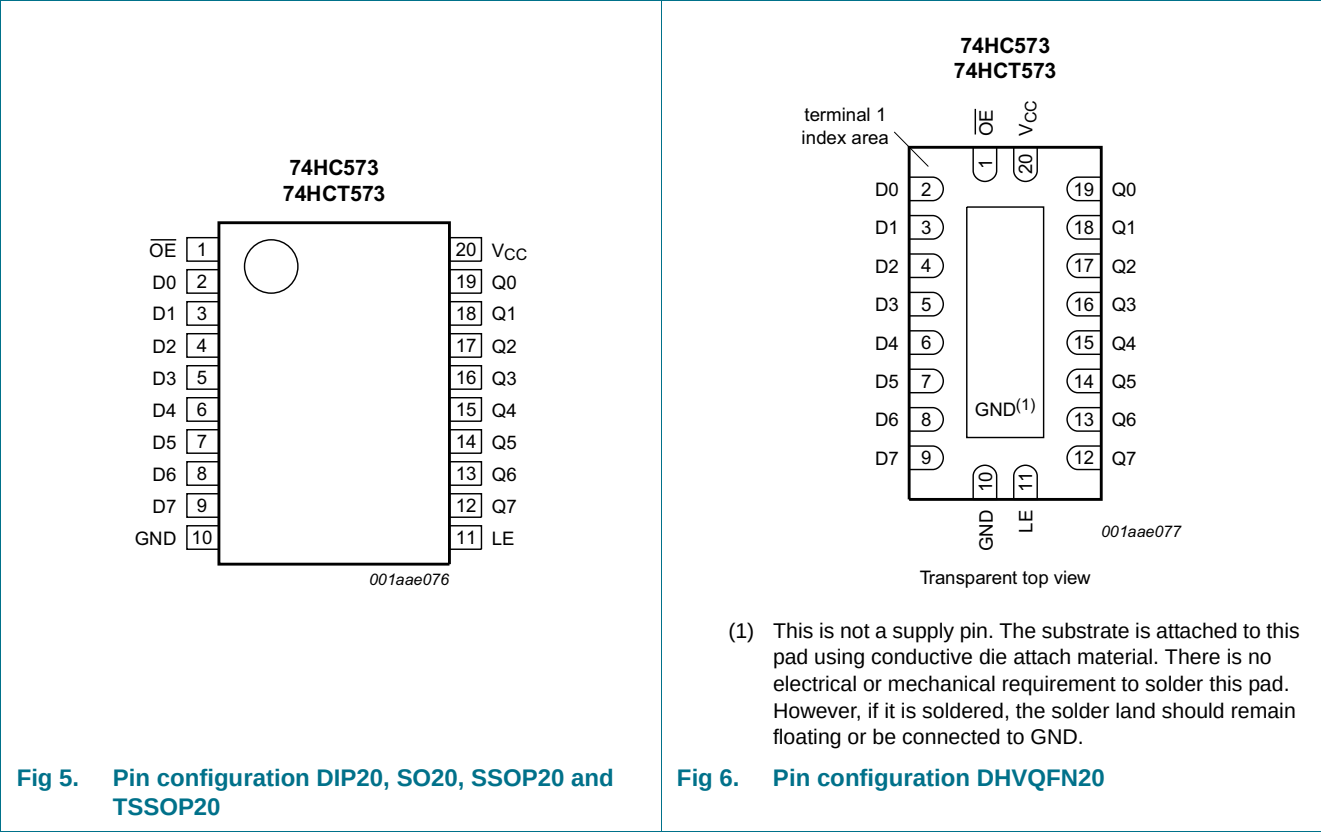


Fig 1. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
$\overline{OE}$	1	3-state output enable input (active LOW)
D[0:7]	2, 3, 4, 5, 6, 7, 8, 9	data input
GND	10	ground (0 V)
LE	11	latch enable input (active HIGH)
Q[0:7]	19, 18, 17, 16, 15, 14, 13, 12	3-state latch output
V _{CC}	20	supply voltage

6. Functional description

Table 3. Function table^[1]

Operating mode	Control		Input	Internal latches	Output
	$\overline{\text{OE}}$	LE	Dn		Qn
Enable and read register (transparent mode)	L	H	L	L	L
			H	H	H
Latch and read register	L	L	L	L	L
			h	H	H
Latch register and disable outputs	H	L	L	L	Z
			h	H	Z

- [1] H = HIGH voltage level;
 h = HIGH voltage level one set-up time prior to the HIGH-to-LOW LE transition;
 L = LOW voltage level;
 l = LOW voltage level one set-up time prior to the HIGH-to-LOW LE transition;
 Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5 \text{ V}$ or $V_I > V_{CC} + 0.5 \text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5 \text{ V}$ or $V_O > V_{CC} + 0.5 \text{ V}$	-	± 20	mA
I_O	output current	$V_O = -0.5 \text{ V}$ to $(V_{CC} + 0.5 \text{ V})$	-	± 35	mA
I_{CC}	supply current		-	+70	mA
I_{GND}	ground current		-	-70	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	DIP20 package ^[1]	-	750	mW
		SO20, SSOP20, TSSOP20 and DHVQFN20 packages ^[2]	-	500	mW

- [1] For DIP20 package: P_{tot} derates linearly with 12 mW/K above 70 °C.
 [2] For SO20: P_{tot} derates linearly with 8 mW/K above 70 °C.
 For SSOP20 and TSSOP20 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
 For DHVQFN20 package: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC573			74HCT573			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	V _{CC}	0	-	V _{CC}	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC573										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = −20 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = −20 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = −20 μA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = −6.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	I _O = −7.8 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
		V _I = V _{IH} or V _{IL}								
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 6.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	I _O = 7.8 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
		V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.5	-	±5.0	-	±10.0	μA

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	8.0	-	80	-	160	μ A
C_I	input capacitance		-	3.5	-					pF
74HCT573										
V_{IH}	HIGH-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V_{IL}	LOW-level input voltage	$V_{CC} = 4.5$ V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V_{OH}	HIGH-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5$ V								
		$I_O = -20$ μ A	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -6$ mA	3.98	4.32	-	3.84	-	3.7	-	V
V_{OL}	LOW-level output voltage	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 4.5$ V								
		$I_O = 20$ μ A	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 6.0$ mA	-	0.16	0.26	-	0.33	-	0.4	V
I_I	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5$ V	-	-	± 0.1	-	± 1.0	-	± 1.0	μ A
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_{CC} = 5.5$ V; $V_O = V_{CC}$ or GND per input pin; other inputs at V_{CC} or GND; $I_O = 0$ A	-	-	± 0.5	-	± 5.0	-	± 10	μ A
I_{CC}	supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	8.0	-	80	-	160	μ A
ΔI_{CC}	additional supply current	$V_I = V_{CC} - 2.1$ V; other inputs at V_{CC} or GND; $V_{CC} = 4.5$ V to 5.5 V; $I_O = 0$ A								
		per input pin; Dn inputs	-	35	126	-	158	-	172	μ A
		per input pin; LE input	-	65	234	-	293	-	319	μ A
		per input pin; $\overline{OE}$ input	-	125	450	-	563	-	613	μ A
C_I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC573										
t _{pd}	propagation delay	Dn to Qn; see Figure 7 [1]								
		V _{CC} = 2.0 V	-	47	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	17	30	-	38	-	45	ns
		V _{CC} = 5 V; C _L = 15 pF	-	14	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	38	ns
t _{pd}	propagation delay	LE to Qn; see Figure 8 [1]								
		V _{CC} = 2.0 V	-	50	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	18	30	-	38	-	45	ns
		V _{CC} = 5 V; C _L = 15 pF	-	15	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	38	ns
t _{en}	enable time	$\overline{OE}$ to Qn; see Figure 9 [2]								
		V _{CC} = 2.0 V	-	44	140	-	175	-	210	ns
		V _{CC} = 4.5 V	-	16	28	-	35	-	42	ns
		V _{CC} = 6.0 V	-	13	24	-	30	-	36	ns
t _{dis}	disable time	$\overline{OE}$ to Qn; see Figure 9 [3]								
		V _{CC} = 2.0 V	-	55	150	-	190	-	225	ns
		V _{CC} = 4.5 V	-	20	30	-	38	-	45	ns
		V _{CC} = 6.0 V	-	16	26	-	33	-	38	ns
t _t	transition time	Qn; see Figure 7 [4]								
		V _{CC} = 2.0 V	-	14	60	-	75	-	90	ns
		V _{CC} = 4.5 V	-	5	12	-	15	-	18	ns
		V _{CC} = 6.0 V	-	4	10	-	13	-	15	ns
t _w	pulse width	LE HIGH; see Figure 8								
		V _{CC} = 2.0 V	80	14	-	100	-	120	-	ns
		V _{CC} = 4.5 V	16	5	-	20	-	24	-	ns
		V _{CC} = 6.0 V	14	4	-	17	-	20	-	ns
t _{su}	set-up time	Dn to LE; see Figure 10								
		V _{CC} = 2.0 V	50	11	-	65	-	75	-	ns
		V _{CC} = 4.5 V	10	4	-	13	-	15	-	ns
		V _{CC} = 6.0 V	9	3	-	11	-	13	-	ns
t _h	hold time	Dn to LE; see Figure 10								
		V _{CC} = 2.0 V	5	3	-	5	-	5	-	ns
		V _{CC} = 4.5 V	5	1	-	5	-	5	-	ns
		V _{CC} = 6.0 V	5	1	-	5	-	5	-	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f = 1 MHz; V _I = GND to V _{CC} [5]	-	26	-	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 11](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HCT573										
t _{pd}	propagation delay	Dn to Qn; see Figure 7 [1]								
		V _{CC} = 4.5 V	-	20	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF	-	17	-	-	-	-	-	ns
t _{pd}	propagation delay	LE to Qn; see Figure 8 [1]								
		V _{CC} = 4.5 V	-	18	35	-	44	-	53	ns
		V _{CC} = 5 V; C _L = 15 pF	-	15	-	-	-	-	-	ns
t _{en}	enable time	$\overline{OE}$ to Qn; see Figure 9 [2]								
		V _{CC} = 4.5 V	-	17	30	-	38	-	45	ns
t _{dis}	disable time	$\overline{OE}$ to Qn; see Figure 9 [3]								
		V _{CC} = 4.5 V	-	18	30	-	38	-	45	ns
t _t	transition time	Qn; see Figure 7 [4]								
		V _{CC} = 4.5 V	-	5	12	-	15	-	18	ns
t _W	pulse width	LE HIGH; see Figure 8								
		V _{CC} = 4.5 V	16	5	-	20	-	24	-	ns
t _{su}	set-up time	Dn to LE; see Figure 10								
		V _{CC} = 4.5 V	13	7	-	16	-	20	-	ns
t _h	hold time	Dn to LE; see Figure 10								
		V _{CC} = 4.5 V	9	4	-	11	-	15	-	ns
C _{PD}	power dissipation capacitance	C _L = 50 pF; f = 1 MHz; V _I = GND to V _{CC} – 1.5 V [5]	-	26	-	-	-	-	-	pF

[1] t_{pd} is the same as t_{PLH} and t_{PHL} .

[2] t_{en} is the same as t_{PZH} and t_{PZL} .

[3] t_{dis} is the same as t_{PLZ} and t_{PHZ} .

[4] t_t is the same as t_{THL} and t_{TLH} .

[5] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

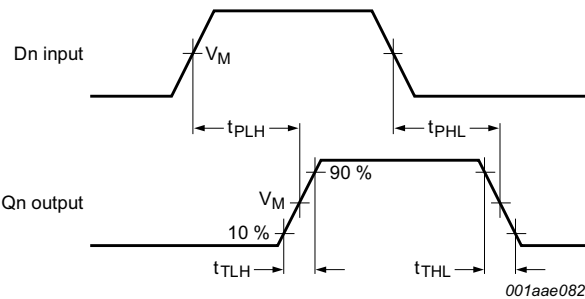
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

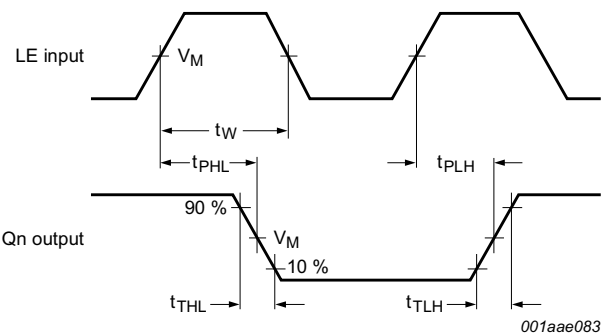
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms



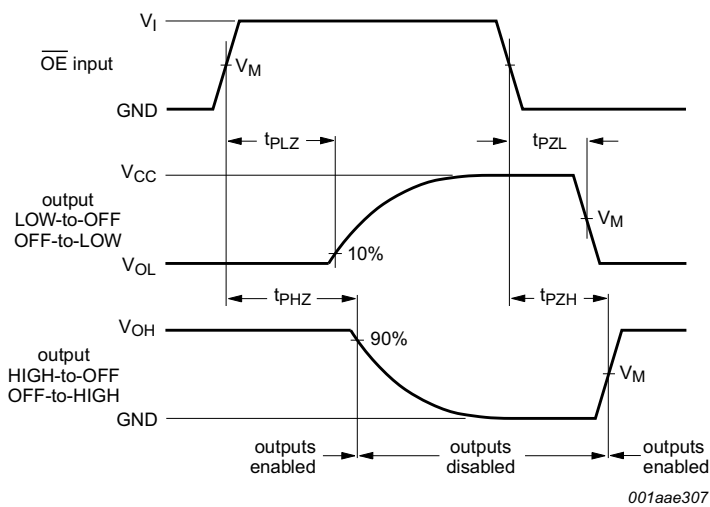
Measurement points are given in [Table 8](#).

Fig 7. Propagation delay data input (Dn) to output (Qn) and output transition time



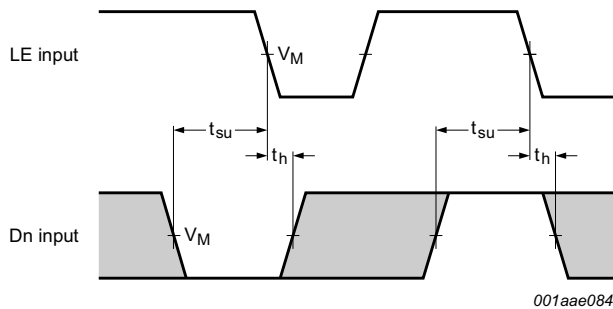
Measurement points are given in [Table 8](#).

Fig 8. Pulse width latch enable input (LE), propagation delay latch enable input (LE) to output (Qn) and output transition time



Measurement points are given in [Table 8](#).
 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 9. Enable and disable times



Measurement points are given in [Table 8](#).
The shaded areas indicate when the input is permitted to change for predictable output performance.

Fig 10. Set-up and hold times for data input (Dn) to latch input (LE)

Table 8. Measurement points

Type	Input	Output
	V_M	V_M
74HC573	$0.5V_{CC}$	$0.5V_{CC}$
74HCT573	1.3 V	1.3 V

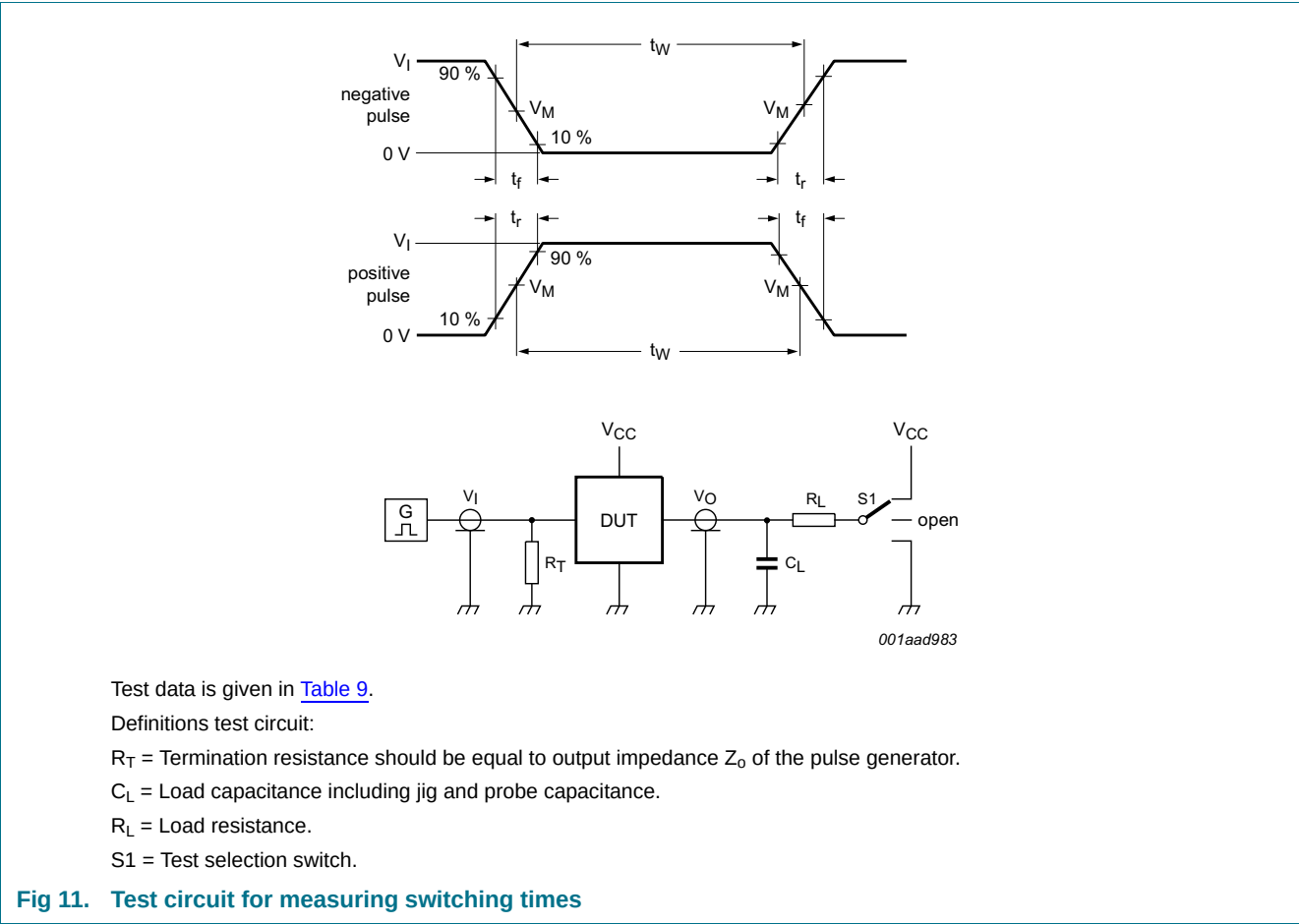


Table 9. Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PHL}, t_{PLH}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC573	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT573	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

12. Package outline

DIP20: plastic dual in-line package; 20 leads (300 mil)

SOT146-1

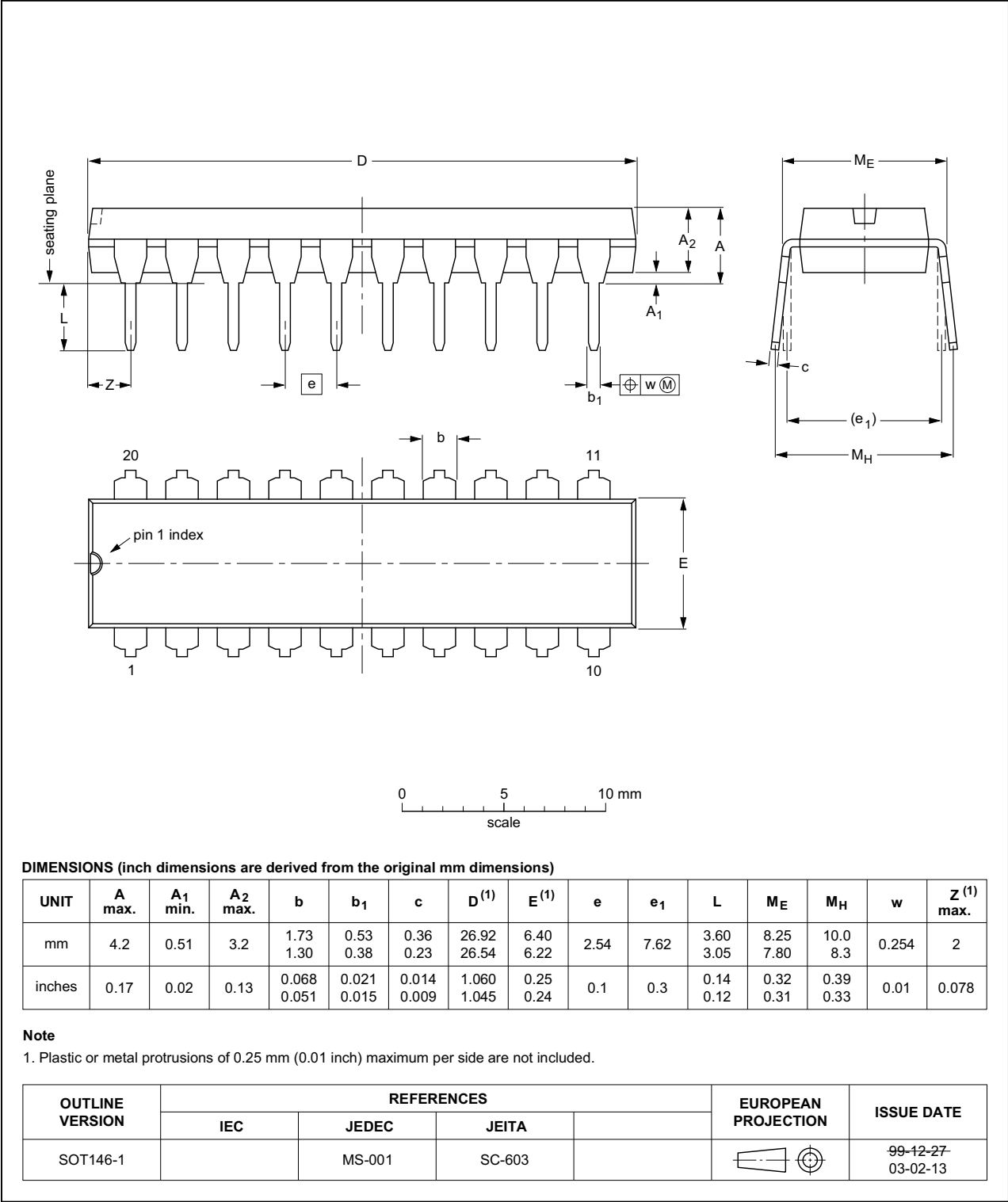


Fig 12. Package outline SOT146-1 (DIP20)

SO20: plastic small outline package; 20 leads; body width 7.5 mm

SOT163-1

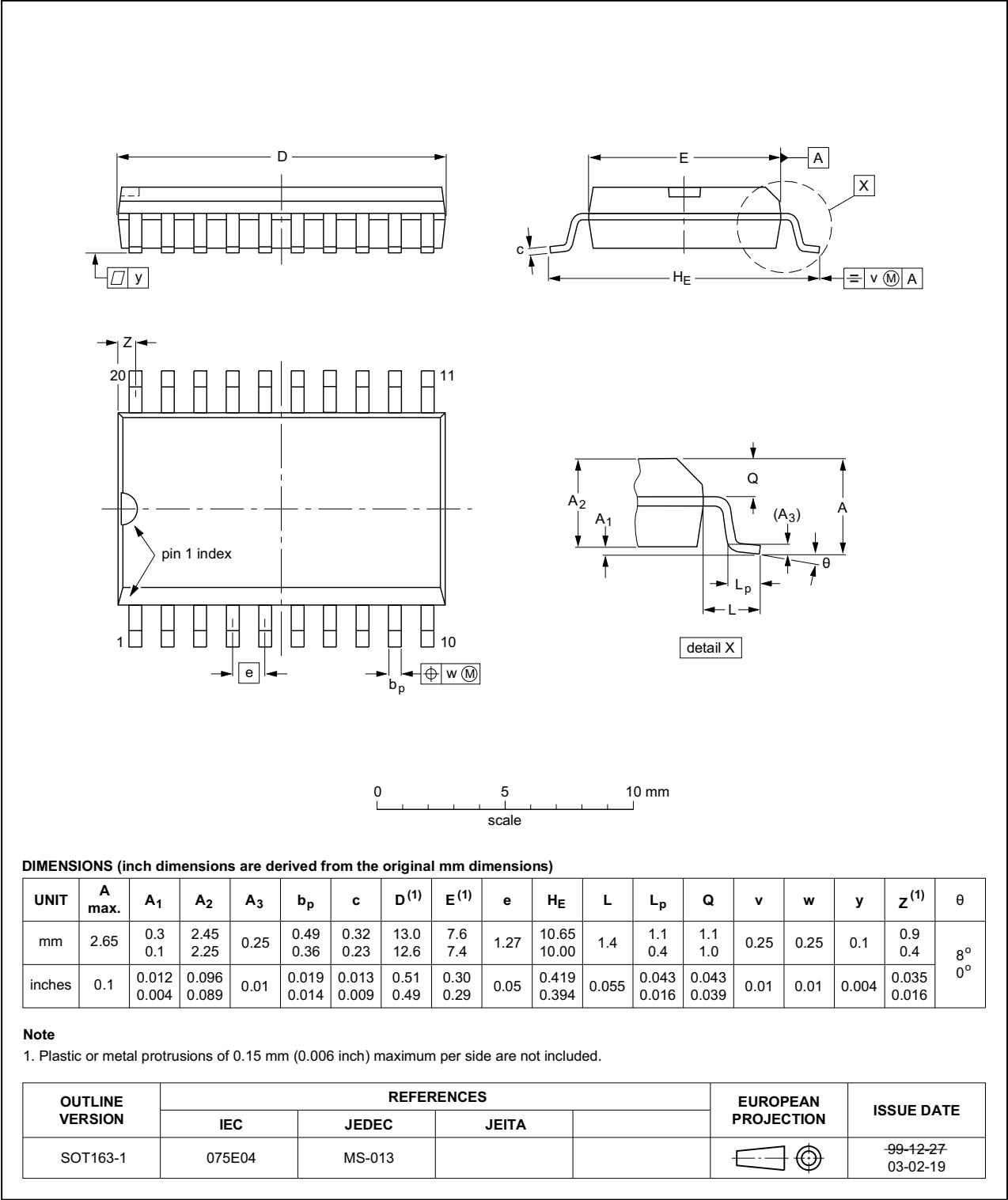


Fig 13. Package outline SOT163-1 (SO20)

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1

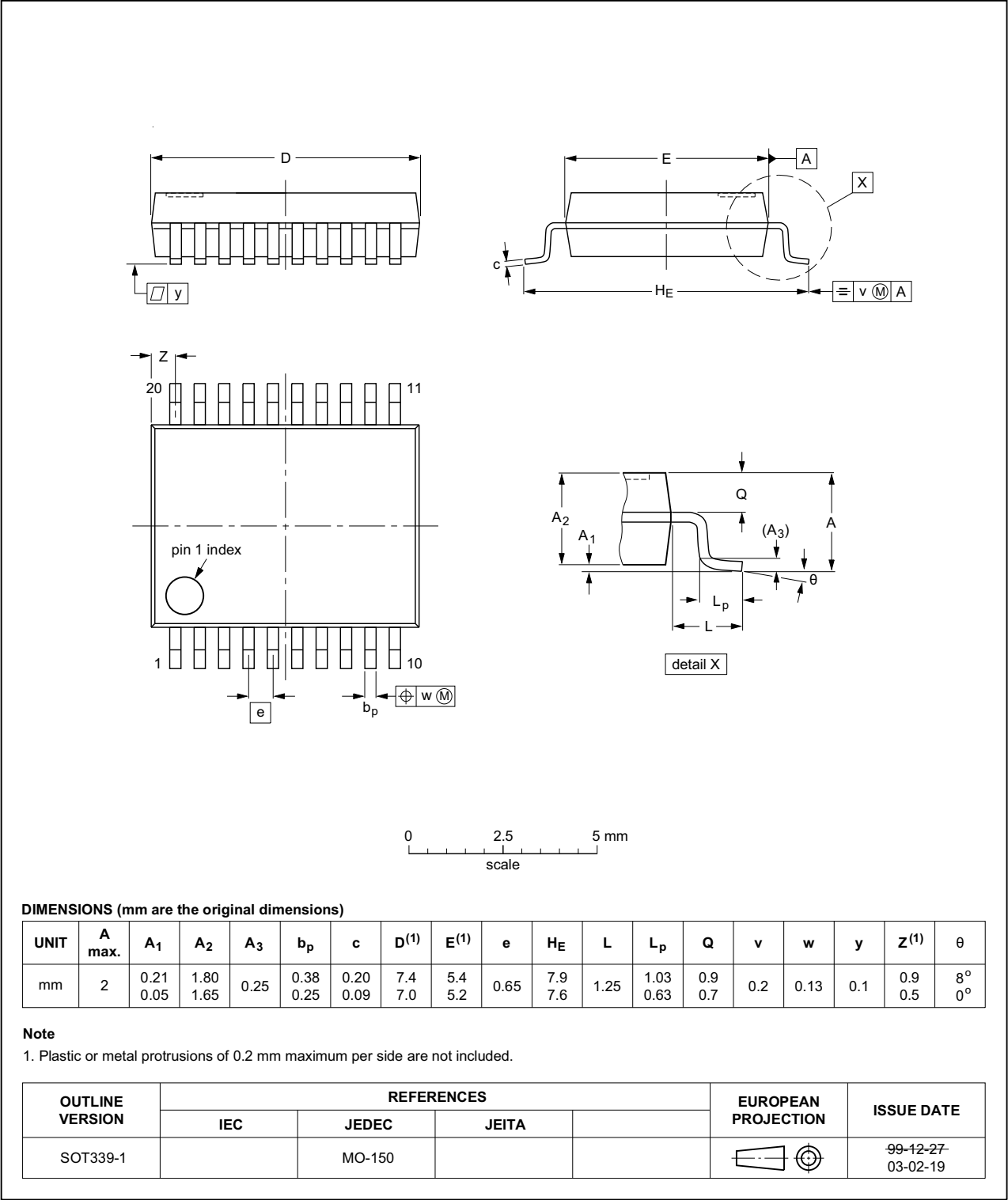


Fig 14. Package outline SOT339-1 (SSOP20)

TSSOP20: plastic thin shrink small outline package; 20 leads; body width 4.4 mm

SOT360-1

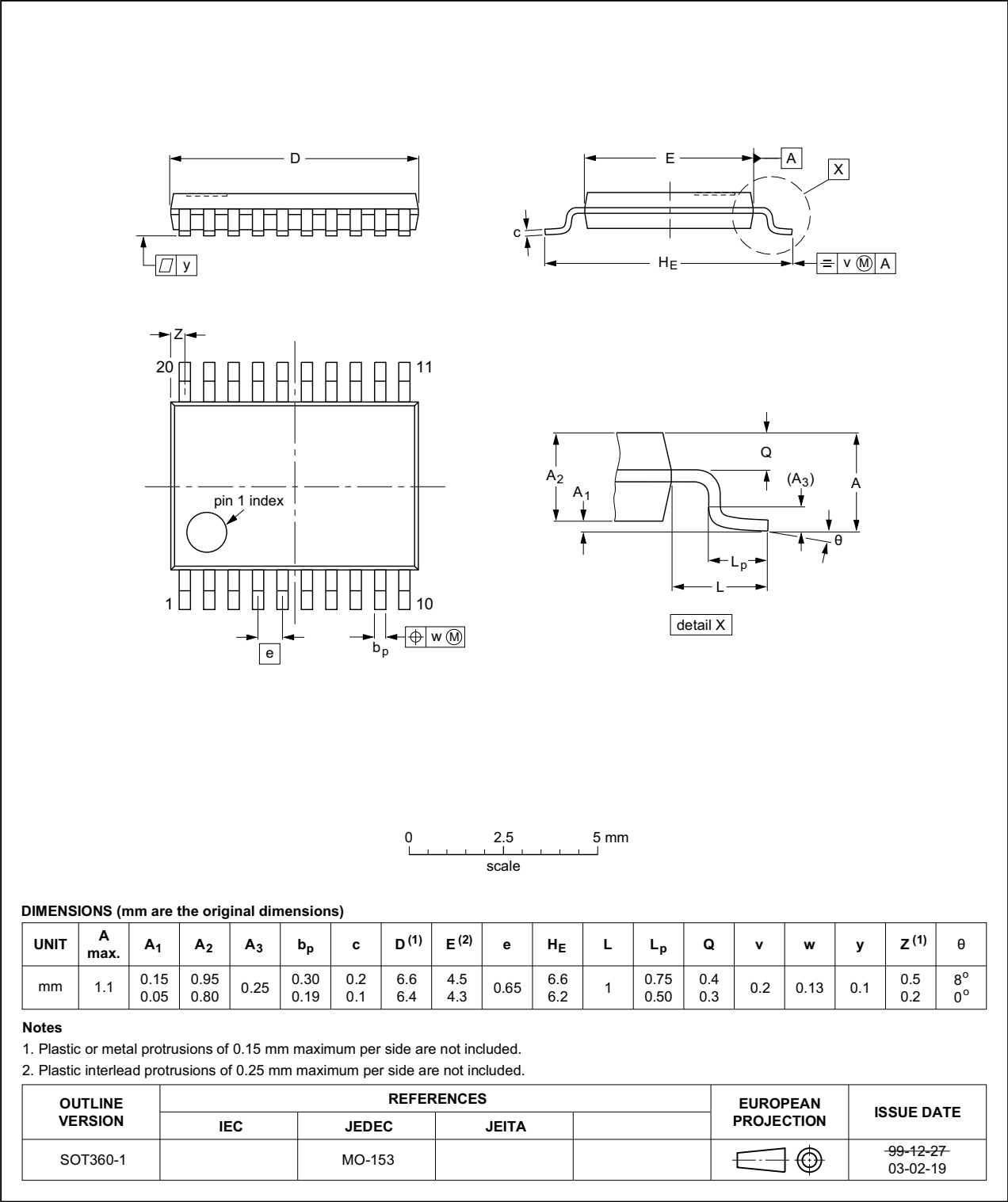


Fig 15. Package outline SOT360-1 (TSSOP20)

DHVQFN20: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;
20 terminals; body 2.5 x 4.5 x 0.85 mm

SOT764-1

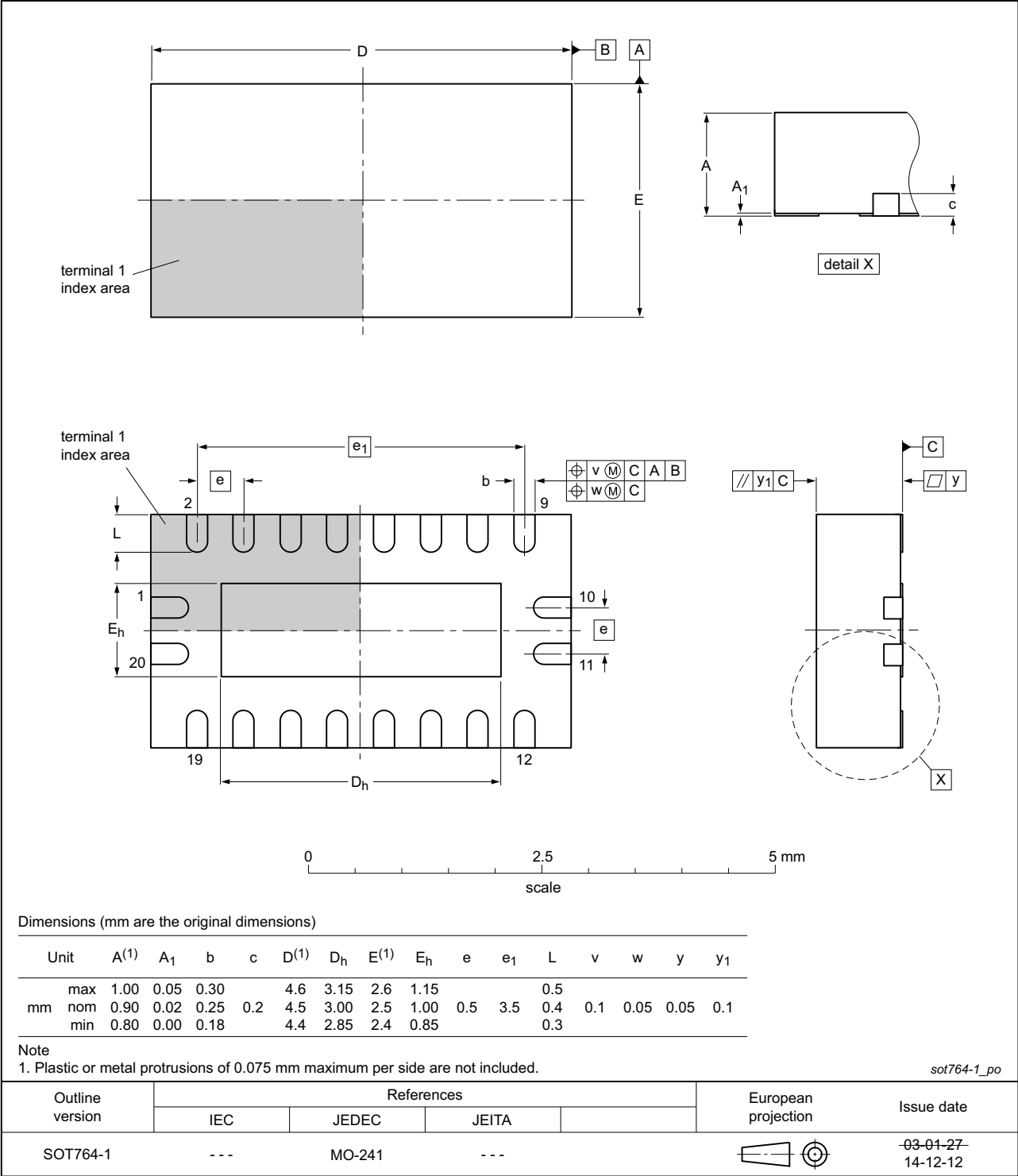


Fig 16. Package outline SOT764-1 (DHVQFN20)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT573 v.6	20150126	Product data sheet	-	74HC_HCT573 v.5
Modifications:	• Table 7: Power dissipation capacitance condition for 74HCT573 is corrected.			
74HC_HCT573 v.5	20120815	Product data sheet	-	74HC_HCT573 v.4
Modifications:	• Alternative descriptive title corrected (errata).			
74HC_HCT573 v.4	20120806	Product data sheet	-	74HC_HCT573 v.3
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.			
74HC_HCT573 v.3	20060117	Product data sheet	-	74HC_HCT573_CNV v.2
74HC_HCT573_CNV v.2	19901201	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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